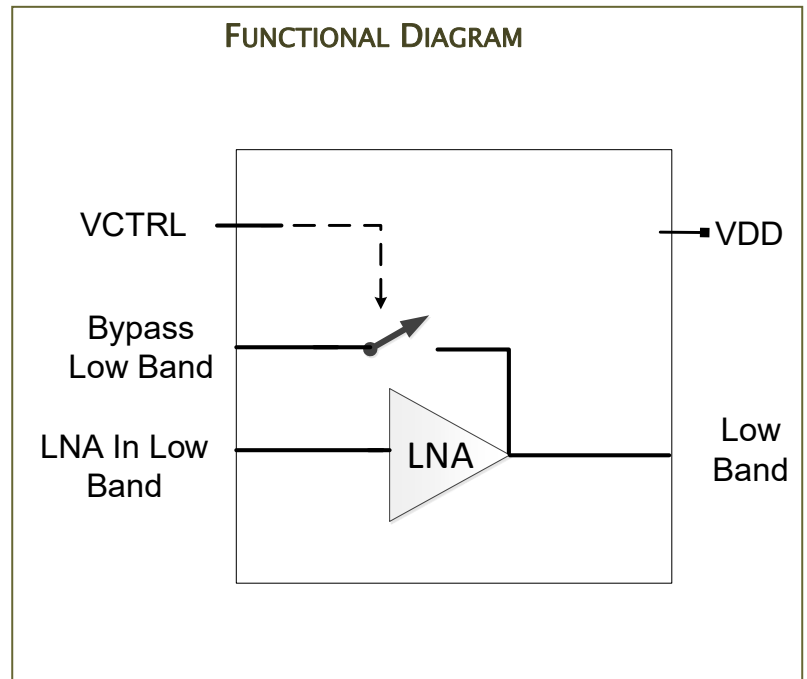


Features

- ☑ CMOS SOI LNA for Low Band cellular applications.
- ☑ High Power Bypass path can handle up to 36dBm which allows it to function both in RX mode and TX mode (for TDD applications)
- ☑ ESD protection on all ports .
- ☑ Noise Figure < 1dB
- ☑ Gain > 15dB
- ☑ Single supply with 2.3V to 4.8V operating range.
- ☑ No external capacitors required if no DC applied on RF lines.
- ☑ Small die for flip-chip assembly.



Description

The FE213601 is a CMOS SOI LNA for cellular applications. It integrates a Low Band LNA and a high power bypass path.

In active mode the LNA provides greater than 15dB gain and less than 1dB Noise Figure. The bypass path has less than 1dB loss and can be used in Rx mode or TX mode with power levels up to 36dBm.

The LNA runs from a single supply with an operating range from 2.3V up to 4.8V. External DC blocking capacitors are not required on the RF ports unless there is a DC voltage externally applied to the ports.

The device is fabricated using a high performance CMOS SOI process optimized for RF front-end applications.

The FE213601 integrates ESD protection on all ports but also integrates ESD protection between the RF ports and the VDD and control ports to support high reliability manufacturing.

The die will be available in die form for flip-chip assembly and will be RoHS compliant to EU Directive 2002/95/EC.

Further Information

Please contact sales@ferfics.com